

SILICON DIODES

T-03-09

General Purpose and Switching Diodes in DO-35 Package & DO-34 Package

Type	Peak Inv. Voltage PIV	Max. Aver. Rectified Current I_o	Power Dissipation at 25 °C	Junction Tempera- ture T_j	Forward Voltage Drop V_F	Reverse Current I_R		Reverse Recovery Time		
						at I_F	at V_R			
	Volts	mA	max. mW	max. °C	max. V	mA	max. nA	Volts	t_{rr} ns	
									Conditions	
1N914	100	75	500	200	1.0	10	25	20	max. 4.0	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_\theta = 100 \Omega$, to $I_R = 1 \text{ mA}$
1N4148	100	150	500	200	1.0	10	25	20	max. 4.0	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_\theta = 100 \Omega$, to $I_R = 1 \text{ mA}$
1N4150	50	200	500	200	1.0	200	100	50	max. 4.0	$I_F = I_R = 10 \text{ to } 200 \text{ mA}$, to $0.1 I_F$
1N4152	40	150	400	175	0.55	0.10	50	30	max. 2.0	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_\theta = 100 \Omega$, to $I_R = 1 \text{ mA}$
1N4154	35	150	500	200	1.0	30	100	25	max. 2.0	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_\theta = 100 \Omega$, to $I_R = 1 \text{ mA}$
1N4448	100	150	500	200	1.0	100	25	20	max. 4.0	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_\theta = 100 \Omega$, to $I_R = 1 \text{ mA}$
1N4450	40	150	400	175	0.54	0.50	50	30	max. 4.0	$I_F = I_R = 10 \text{ mA}$, to $I_R = 1 \text{ mA}$
1N4454	75	150	400	175	1.0	10	100	50	max. 4.0	$I_F = I_R = 10 \text{ mA}$, to $I_R = 1 \text{ mA}$

General Purpose and Switching Diodes in MiniMELF Package

Type	Peak Inv. Voltage PIV	Max. Aver. Rectified Current I_o	Power Dissipation at 25 °C	Junction Tempera- ture T_j	Forward Voltage Drop V_F	Reverse Current I_R	Reverse Recovery Time			
					at I_F	at V_R				
	Volts	mA	max. mW	max. °C	max. V	mA	max. nA	Volts	t_{rr} ns	Conditions
LL4148	100	150	500	200	1.0	10	25	20	max. 4.0	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_\theta = 100 \Omega$, to $I_R = 1 \text{ mA}$
LL4150	50	200	500	200	1.0	200	100	50	max. 4.0	$I_F = I_R = 10 \text{ to } 200 \text{ mA}$, to $0.1 I_F$
LL4152	40	150	400	175	0.55	0.10	50	30	max. 2.0	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_\theta = 100 \Omega$, to $I_R = 1 \text{ mA}$
LL4154	35	150	500	200	1.0	30	100	25	max. 2.0	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_\theta = 100 \Omega$, to $I_R = 1 \text{ mA}$
LL4448	100	150	500	200	1.0	100	25	20	max. 4.0	$I_F = 10 \text{ mA}$, $V_R = 6 \text{ V}$, $R_\theta = 100 \Omega$, to $I_R = 1 \text{ mA}$
LL4450	40	150	400	175	0.54	0.50	50	30	max. 4.0	$I_F = I_R = 10 \text{ mA}$, to $I_R = 1 \text{ mA}$
LL4454	75	150	400	175	1.0	10	100	50	max. 4.0	$I_F = I_R = 10 \text{ mA}$, to $I_R = 1 \text{ mA}$

SCHOTTKY DIODES

Silicon Schottky Barrier Diodes in DO-35 Package

for general purpose applications with low forward voltage drop and very fast switching times.

Using the type designations LL101A, LL103A and so on, these Schottky Barrier diodes are available in the MiniMELF package with the same electrical characteristics.

Type	Peak Inv. Voltage PIV	Power Dissipation at 25 °C	Junction and Storage Temp.	Forward Voltage Drop V _F at I _F				Reverse Current I _R at V _R		Capacitance at V _F = V _R = 0, f = 1 MHz	Reverse Recovery Time t _r	
	Volts	max. mW	max. °C	max. V	at mA	max. V	at mA	max. µA	at V	max. pF	max. ns	Conditions
SD101A*	60	400	200	0.41	1	1.0	15	0.2	50	2.0	1	I _F = I _R = 5 mA to 0.1 I _R
SD101B	50	400	200	0.40	1	0.95	15	0.2	40	2.1	1	I _F = I _R = 5 mA to 0.1 I _R
SD101C	40	400	200	0.39	1	0.90	15	0.2	30	2.2	1	I _F = I _R = 5 mA to 0.1 I _R
SD103A	40	400	125	0.37	20	0.6	200	5.0	30	50	10	I _F = I _R = 200 mA to 0.1 I _R
SD103B	30	400	125	0.37	20	0.6	200	5.0	20	50	10	I _F = I _R = 200 mA to 0.1 I _R
SD103C	20	400	125	0.37	20	0.6	200	5.0	10	50	10	I _F = I _R = 200 mA to 0.1 I _R

*JEDEC Equivalent: 1N6263